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NXP USA Inc. - MPC8347ECVVAJFB Datasheet



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Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	533MHz
Co-Processors/DSP	Security; SEC
RAM Controllers	DDR
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	672-LBGA
Supplier Device Package	672-LBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8347ecvvajfb

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5 **RESET Initialization**

This section describes the DC and AC electrical specifications for the reset initialization timing and electrical requirements of the MPC8347E.

5.1 **RESET DC Electrical Characteristics**

Table 8 provides the DC electrical characteristics for the RESET pins of the MPC8347E.

Table 8.	RESET	Pins DC	Electrical	Characteristics'

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V _{IH}		2.0	OV _{DD} + 0.3	V
Input low voltage	V _{IL}		-0.3	0.8	V
Input current	I _{IN}			±5	μA
Output high voltage ²	V _{OH}	I _{OH} = -8.0 mA	2.4	—	V
Output low voltage	V _{OL}	I _{OL} = 8.0 mA	_	0.5	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	_	0.4	V

Notes:

1. This table applies for pins PORESET, HRESET, SRESET, and QUIESCE.

2. HRESET and SRESET are open drain pins, thus V_{OH} is not relevant for those pins.

5.2 **RESET AC Electrical Characteristics**

Table 9 provides the reset initialization AC timing specifications of the MPC8347E.

Table 9. RESET Initialization Timing Specifications

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of HRESET or SRESET (input) to activate reset flow	32	—	t _{PCI_SYNC_IN}	1
Required assertion time of PORESET with stable clock applied to CLKIN when the MPC8347E is in PCI host mode	32	—	^t CLKIN	2
Required assertion time of PORESET with stable clock applied to PCI_SYNC_IN when the MPC8347E is in PCI agent mode	32	_	t _{PCI_SYNC_IN}	1
HRESET/SRESET assertion (output)	512	—	t _{PCI_SYNC_IN}	1
HRESET negation to SRESET negation (output)	16	—	t _{PCI_SYNC_IN}	1
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of PORESET when the MPC8347E is in PCI host mode	4	_	^t CLKIN	2
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of PORESET when the MPC8347E is in PCI agent mode	4	_	^t pci_sync_in	1

Parameter/Condition	Min	Мах	Unit	Notes
Input hold time for POR configuration signals with respect to negation of HRESET	0	_	ns	
Time for the MPC8347E to turn off POR configuration signals with respect to the assertion of $\overline{\text{HRESET}}$	—	4	ns	3
Time for the MPC8347E to turn on POR configuration signals with respect to the negation of HRESET	1	_	^t PCI_SYNC_IN	1, 3

Table 9. RESET Initialization Timing Specifications (continued)

Notes:

1. t_{PCI_SYNC_IN} is the clock period of the input clock applied to PCI_SYNC_IN. In PCI host mode, the primary clock is applied to the CLKIN input, and PCI_SYNC_IN period depends on the value of CFG_CLKIN_DIV. See the *MPC8349E PowerQUICC™ II Pro Integrated Host Processor Family Reference Manual*.

- 2. t_{CLKIN} is the clock period of the input clock applied to CLKIN. It is valid only in PCI host mode. See the MPC8349E PowerQUICC™ II Pro Integrated Host Processor Family Reference Manual.
- 3. POR configuration signals consist of CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV.

Table 10 lists the PLL and DLL lock times.

Table 10. PLL and DLL Lock Times

Parameter/Condition	Min	Мах	Unit	Notes
PLL lock times	—	100	μs	
DLL lock times	7680	122,880	csb_clk cycles	1, 2

Notes:

1. DLL lock times are a function of the ratio between the output clock and the coherency system bus clock (csb_clk). A 2:1 ratio results in the minimum and an 8:1 ratio results in the maximum.

2. The csb_clk is determined by the CLKIN and system PLL ratio. See Section 19, "Clocking."



Figure 6. DDR AC Test Load

Table 15 shows the DDR SDRAM measurement conditions.

Table 15. DDR SDRAM Measurement Conditions

Symbol	DDR	Unit	Notes
V _{TH}	MV _{REF} ± 0.31 V	V	1
V _{OUT}	$0.5 imes GV_{DD}$	V	2

Notes:

1. Data input threshold measurement point.

2. Data output measurement point.

Figure 7 shows the DDR SDRAM output timing diagram for source synchronous mode.



Figure 7. DDR SDRAM Output Timing Diagram for Source Synchronous Mode

Table 16 provides approximate delay information that can be expected for the address and command signals of the DDR controller for various loadings, which can be useful for a system utilizing the DLL. These numbers are the result of simulations for one topology. The delay numbers will strongly depend on the topology used. These delay numbers show the total delay for the address and command to arrive at the DRAM devices. The actual delay could be different than the delays seen in simulation, depending on the system topology. If a heavily loaded system is used, the DLL loop may need to be adjusted to meet setup requirements at the DRAM.

DDR SDRAM

Load	Delay	Unit
4 devices (12 pF)	3.0	ns
9 devices (27 pF)	3.6	ns
36 devices (108 pF) + 40 pF compensation capacitor	5.0	ns
36 devices (108 pF) + 80 pF compensation capacitor	5.2	ns

Table 16. Expected Delays for Address/Command

8 Ethernet: Three-Speed Ethernet, MII Management

This section provides the AC and DC electrical characteristics for three-speeds (10/100/1000 Mbps) and MII management.

8.1 Three-Speed Ethernet Controller (TSEC)— GMII/MII/TBI/RGMII/RTBI Electrical Characteristics

The electrical characteristics specified here apply to the gigabit media independent interface (GMII), the media independent interface (MII), ten-bit interface (TBI), reduced gigabit media independent interface (RGMII), and reduced ten-bit interface (RTBI) signals except management data input/output (MDIO) and management data clock (MDC). The MII, GMII, and TBI interfaces are defined for 3.3 V, and the RGMII and RTBI interfaces are defined for 2.5 V. The RGMII and RTBI interfaces follow the Hewlett-Packard *Reduced Pin-Count Interface for Gigabit Ethernet Physical Layer Device Specification*, Version 1.2a (9/22/2000). The electrical characteristics for MDIO and MDC are specified in Section 8.3, "Ethernet Management Interface Electrical Characteristics."

8.1.1 **TSEC DC Electrical Characteristics**

GMII, MII, TBI, RGMII, and RTBI drivers and receivers comply with the DC parametric attributes specified in Table 19 and Table 20. The RGMII and RTBI signals in Table 20 are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Parameter	Symbol	Conditions		Min	Мах	Unit
Supply voltage 3.3 V	LV_{DD}^2	—		2.97	3.63	V
Output high voltage	V _{OH}	I _{OH} = -4.0 mA	$LV_{DD} = Min$	2.40	LV _{DD} + 0.3	V
Output low voltage	V _{OL}	I _{OL} = 4.0 mA	LV _{DD} = Min	GND	0.50	V
Input high voltage	V _{IH}	—	—	2.0	LV _{DD} + 0.3	V
Input low voltage	V _{IL}	—	—	-0.3	0.90	V
Input high current	IIH	$V_{IN}^{1} = LV_{DD}$		-	40	μA
Input low current	IIL	V _{IN} ¹ =	GND	-600	—	μA

Table 19. GMII/TBI and MII DC Electrical Characteristics

Notes:

1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

2. GMII/MII pins not needed for RGMII or RTBI operation are powered by the $\ensuremath{\mathsf{OV}_{\mathsf{DD}}}$ supply.

Parameters	Symbol	Conditions		Min	Мах	Unit
Supply voltage 2.5 V	LV _{DD}	_		2.37	2.63	V
Output high voltage	V _{OH}	$I_{OH} = -1.0 \text{ mA}$ $LV_{DD} = Min$		2.00	LV _{DD} + 0.3	V
Output low voltage	V _{OL}	$I_{OL} = 1.0 \text{ mA}$ $LV_{DD} = Min$		GND – 0.3	0.40	V
Input high voltage	V _{IH}	—	— LV _{DD} = Min		LV _{DD} + 0.3	V
Input low voltage	V _{IL}	—	— LV _{DD} = Min		0.70	V
Input high current	I _{IH}	$V_{IN}^{1} = LV_{DD}$		—	10	μA
Input low current	I	V _{IN} ¹ =	GND	-15	_	μA

Table 20. RGMII/RTBI (When Operating at 2.5 V) DC Electrical Characteristics

Note:

1. The symbol V_{IN} , in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

8.2 GMII, MII, TBI, RGMII, and RTBI AC Timing Specifications

The AC timing specifications for GMII, MII, TBI, RGMII, and RTBI are presented in this section.

8.2.1 GMII Timing Specifications

This section describes the GMII transmit and receive AC timing specifications.

8.2.1.1 GMII Transmit AC Timing Specifications

Table 21 provides the GMII transmit AC timing specifications.

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit
GTX_CLK clock period	t _{GTX}	—	8.0	—	ns
GTX_CLK duty cycle	t _{GTXH} /t _{GTX}	43.75	—	56.25	%
GTX_CLK to GMII data TXD[7:0], TX_ER, TX_EN delay	^t GTKHDX	0.5	—	5.0	ns
GTX_CLK clock rise time, V _{IL} (min) to V _{IH} (max)	t _{GTXR}	—	—	1.0	ns
GTX_CLK clock fall time, V _{IH} (max) to V _{IL} (min)	t _{GTXF}	—	—	1.0	ns
GTX_CLK125 clock period	t _{G125} 2	—	8.0	—	ns
GTX_CLK125 reference clock duty cycle measured at $LV_{DD}/2$	t _{G125H} /t _{G125}	45	—	55	%

Notes:

1. The symbols for timing specifications follow the pattern t_{(first two letters of functional block)(signal)(state)(reference)(state)} for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{GTKHDV} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) reaching the valid state (V) to state or setup time. Also, t_{GTKHDX} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the time date input signals (D) reaching the valid state (V) to state or setup time. Also, t_{GTKHDX} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) going invalid (X) or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{GTX} represents the GMII(G) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

2. This symbol represents the external GTX_CLK125 signal and does not follow the original symbol naming convention.

Table 21. GMII Transmit AC Timing Specifications

Figure 14 shows the TBI receive AC timing diagram.



Figure 14. TBI Receive AC Timing Diagram

8.2.4 RGMII and RTBI AC Timing Specifications

Table 27 presents the RGMII and RTBI AC timing specifications.

Table 27. RGMII and RTBI AC Timing Specifications

At recommended operating conditions with LV_{DD} of 2.5 V \pm 5%.

Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit
Data to clock output skew (at transmitter)	t _{SKRGT}	-0.5	—	0.5	ns
Data to clock input skew (at receiver) ²	t _{SKRGT}	1.0	—	2.8	ns
Clock cycle duration ³	t _{RGT}	7.2	8.0	8.8	ns
Duty cycle for 1000Base-T ^{4, 5}	t _{RGTH} /t _{RGT}	45	50	55	%
Duty cycle for 10BASE-T and 100BASE-TX ^{3, 5}	t _{RGTH} /t _{RGT}	40	50	60	%
Rise time (20%–80%)	t _{RGTR}	—	—	0.75	ns
Fall time (20%–80%)	t _{RGTF}	—	—	0.75	ns
GTX_CLK125 reference clock period	t _{G12} 6	—	8.0	—	ns
GTX_CLK125 reference clock duty cycle	t _{G125H} /t _{G125}	47	—	53	%

Notes:

 In general, the clock reference symbol for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Also, the notation for rise (R) and fall (F) times follows the clock symbol. For symbols representing skews, the subscript is SK followed by the clock being skewed (RGT).

2. This implies that PC board design requires clocks to be routed so that an additional trace delay of greater than 1.5 ns is added to the associated clock signal.

3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns \pm 40 ns and 40 ns \pm 4 ns, respectively.

- 4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned.
- 5. Duty cycle reference is $LV_{DD}/2$.

6. This symbol represents the external GTX_CLK125 and does not follow the original symbol naming convention.

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to the MII management interface signals management data input/output (MDIO) and management data clock (MDC). The electrical characteristics for GMII, RGMII, TBI and RTBI are specified in Section 8.1, "Three-Speed Ethernet Controller (TSEC)—GMII/MII/TBI/RGMII/RTBI Electrical Characteristics."

8.3.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 2.5 or 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in Table 28 and Table 29.

Parameter	Symbol	Conditions		Min	Мах	Unit
Supply voltage (2.5 V)	LV _{DD}	—		2.37	2.63	V
Output high voltage	V _{OH}	$I_{OH} = -1.0 \text{ mA}$	$LV_{DD} = Min$	2.00	LV _{DD} + 0.3	V
Output low voltage	V _{OL}	I _{OL} = 1.0 mA	LV _{DD} = Min	GND – 0.3	0.40	V
Input high voltage	V _{IH}	—	LV _{DD} = Min	1.7	—	V
Input low voltage	V _{IL}	—	LV _{DD} = Min	-0.3	0.70	V
Input high current	I _{IH}	$V_{IN}^{1} = LV_{DD}$		—	10	μA
Input low current	I _{IL}	$V_{IN} = LV_{DD}$		-15	—	μA

Table 28. MII Management DC Electrical Characteristics Powered at 2.5 V

Note:

1. The symbol V_{IN} , in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

Table 29	MII Manad	nement DC	Flectrical	Characteristics	Powered at 3.3 V
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Parameter	Symbol	Conditions		Min	Мах	Unit		
Supply voltage (3.3 V)	LV _{DD}	—		2.97	3.63	V		
Output high voltage	V _{OH}	$I_{OH} = -1.0 \text{ mA}$ $LV_{DD} = Min$		2.10	LV _{DD} + 0.3	V		
Output low voltage	V _{OL}	I _{OL} = 1.0 mA LV _{DD} = Min		GND	0.50	V		
Input high voltage	V _{IH}	—		2.00	—	V		
Input low voltage	V _{IL}	_		—		—	0.80	V
Input high current	I _{IH}	LV _{DD} = Max	$V_{IN}^{1} = 2.1 V$	—	40	μA		
Input low current	IIL	$LV_{DD} = Max$ $V_{IN} = 0.5 V$		-600	—	μA		

Note:

1. The symbol V_{IN} , in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

9 USB

This section provides the AC and DC electrical specifications for the USB interface of the MPC8347E.

9.1 USB DC Electrical Characteristics

Table 31 provides the DC electrical characteristics for the USB interface.

Parameter	Symbol	Min	Мах	Unit
High-level input voltage	V _{IH}	2	OV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.8	V
Input current	I _{IN}	—	±5	μA
High-level output voltage, $I_{OH} = -100 \ \mu A$	V _{OH}	OV _{DD} – 0.2	-	V
Low-level output voltage, $I_{OL} = 100 \ \mu A$	V _{OL}	—	0.2	V

Table 31. USB DC Electrical Characteristics

9.2 USB AC Electrical Specifications

Table 32 describes the general timing parameters of the USB interface of the MPC8347E.

Table 32.	USB C	General	Timing	Parameters	(ULPI	Mode	Only)
					\-		

Parameter	Symbol ¹	Min	Мах	Unit	Notes
USB clock cycle time	t _{USCK}	15	-	ns	2–5
Input setup to USB clock—all inputs	t _{USIVKH}	4	-	ns	2–5
Input hold to USB clock—all inputs	t _{USIXKH}	1	-	ns	2–5
USB clock to output valid—all outputs	t _{USKHOV}	—	7	ns	2–5
Output hold from USB clock—all outputs	t _{USKHOX}	2		ns	2–5

Notes:

 The symbols for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{USIXKH} symbolizes USB timing (US) for the input (I) to go invalid (X) with respect to the time the USB clock reference (K) goes high (H). Also, t_{USKHOX} symbolizes USB timing (US) for the USB clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
</sub>

2. All timings are in reference to USB clock.

- 3. All signals are measured from $OV_{DD}/2$ of the rising edge of the USB clock to $0.4 \times OV_{DD}$ of the signal in question for 3.3 V signaling levels.
- 4. Input timings are measured at the pin.
- 5. For active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to that of the leakage current specification.

18.3 Package Parameters for the MPC8347E PBGA

The package parameters are as provided in the following list. The package type is $29 \text{ mm} \times 29 \text{ mm}$, 620 plastic ball grid array (PBGA).

Package outline	$29 \text{ mm} \times 29 \text{ mm}$
Interconnects	620
Pitch	1.00 mm
Module height (maximum)	2.46 mm
Module height (typical)	2.23 mm
Module height (minimum)	2.00 mm
Solder balls	62 Sn/36 Pb/2 Ag (ZQ package)
	95.5 Sn/0.5 Cu/4Ag (VR package)
Ball diameter (typical)	0.60 mm

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI1_IRDY	E13	I/O	OV _{DD}	5
PCI1_STOP	C13	I/O	OV _{DD}	5
PCI1_DEVSEL	B13	I/O	OV _{DD}	5
PCI1_IDSEL	C17	I	OV _{DD}	
PCI1_SERR	C12	I/O	OV _{DD}	5
PCI1_PERR	B12	I/O	OV _{DD}	5
PCI1_REQ[0]	A21	I/O	OV _{DD}	
PCI1_REQ[1]/CPCI1_HS_ES	C19	I	OV _{DD}	
PCI1_REQ[2:4]	C18, A19, E20	I	OV _{DD}	
PCI1_GNT0	B20	I/O	OV _{DD}	
PCI1_GNT1/CPCI1_HS_LED	C20	0	OV _{DD}	
PCI1_GNT2/CPCI1_HS_ENUM	B19	0	OV _{DD}	
PCI1_GNT[3:4]	A20, E18	0	OV _{DD}	
M66EN	L26	I	OV _{DD}	
	DDR SDRAM Memory Interface			
MDQ[0:63]	AC25, AD27, AD25, AH27, AE28, AD26, AD24, AF27, AF25, AF28, AH24, AG26, AE25, AG25, AH26, AH25, AG22, AH22, AE21, AD19, AE22, AF23, AE19, AG20, AG19, AD17, AE16, AF16, AF18, AG18, AH17, AH16, AG9, AD12, AG7, AE8, AD11, AH9, AH8, AF6, AF8, AE6, AF1, AE4, AG8, AH3, AG3, AG4, AH2, AD7, AB4, AB3, AG1, AD5, AC2, AC1, AC4, AA3, Y4, AA4, AB1, AB2, Y5, Y3	I/O	GV _{DD}	
MECC[0:4]/MSRCID[0:4]	AG13, AE14, AH12, AH10, AE15	I/O	GV _{DD}	
MECC[5]/MDVAL	AH14	I/O	GV _{DD}	
MECC[6:7]	AE13, AH11	I/O	GV _{DD}	
MDM[0:8]	AG28, AG24, AF20, AG17, AE9, AH5, AD1, AA2, AG12	0	GV _{DD}	
MDQS[0:8]	AE27, AE26, AE20, AH18, AG10, AF5, AC3, AA1, AH13	I/O	GV _{DD}	
MBA[0:1]	AF10, AF11	0	GV _{DD}	
MA[0:14]	AF13, AF15, AG16, AD16, AF17, AH20, AH19, AH21, AD18, AG21, AD13, AF21, AF22, AE1, AA5	0	GV _{DD}	
MWE	AD10	0	GV _{DD}	
MRAS	AF7	0	GV _{DD}	

Table 52. MPC8347E (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes				
General Purpose I/O Timers								
GPIO1[0]/GTM1_TIN1/GTM2_TIN2	D27	I/O	OV _{DD}					
GPIO1[1]/GTM1_TGATE1/GTM2_TGATE2	E26	I/O	OV _{DD}					
GPIO1[2]/GTM1_TOUT1	D28	I/O	OV _{DD}					
GPIO1[3]/GTM1_TIN2/GTM2_TIN1	G25	I/O	OV _{DD}					
GPIO1[4]/GTM1_TGATE2/GTM2_TGATE1	J24	I/O	OV _{DD}					
GPIO1[5]/GTM1_TOUT2/GTM2_TOUT1	F26	I/O	OV _{DD}					
GPIO1[6]/GTM1_TIN3/GTM2_TIN4	E27	I/O	OV _{DD}					
GPIO1[7]/GTM1_TGATE3/GTM2_TGATE4	E28	I/O	OV _{DD}					
GPIO1[8]/GTM1_TOUT3	H25	I/O	OV _{DD}					
GPIO1[9]/GTM1_TIN4/GTM2_TIN3	F27	I/O	OV _{DD}					
GPIO1[10]/GTM1_TGATE4/GTM2_TGATE3	K24	I/O	OV _{DD}					
GPIO1[11]/GTM1_TOUT4/GTM2_TOUT3	G26	I/O	OV _{DD}					
	USB Port 1	L		1				
MPH1_D0_ENABLEN/DR_D0_ENABLEN	C28	I/O	OV _{DD}					
MPH1_D1_SER_TXD/DR_D1_SER_TXD	F25	I/O	OV _{DD}					
MPH1_D2_VMO_SE0/DR_D2_VMO_SE0	B28	I/O	OV _{DD}					
MPH1_D3_SPEED/DR_D3_SPEED	C27	I/O	OV _{DD}					
MPH1_D4_DP/DR_D4_DP	D26	I/O	OV _{DD}					
MPH1_D5_DM/DR_D5_DM	E25	I/O	OV _{DD}					
MPH1_D6_SER_RCV/DR_D6_SER_RCV	C26	I/O	OV _{DD}					
MPH1_D7_DRVVBUS/DR_D7_DRVVBUS	D25	I/O	OV _{DD}					
MPH1_NXT/DR_SESS_VLD_NXT	B26	I	OV _{DD}					
MPH1_DIR_DPPULLUP/ DR_XCVR_SEL_DPPULLUP	E24	I/O	OV _{DD}					
MPH1_STP_SUSPEND/ DR_STP_SUSPEND	A27	0	OV _{DD}					
MPH1_PWRFAULT/ DR_RX_ERROR_PWRFAULT	C25	I	OV _{DD}					
MPH1_PCTL0/DR_TX_VALID_PCTL0	A26	0	OV _{DD}					
MPH1_PCTL1/DR_TX_VALIDH_PCTL1	B25	0	OV _{DD}					
MPH1_CLK/DR_CLK	A25	I	OV _{DD}					
	USB Port 0	1	1	1				
MPH0_D0_ENABLEN/DR_D8_CHGVBUS	D24	I/O	OV _{DD}					
MPH0_D1_SER_TXD/DR_D9_DCHGVBUS	C24	I/O	OV _{DD}					

Table 52. MPC8347E (PBGA) Pinout Listing (continued)

Table 52. MPC8347E (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes			
TSEC1_TXD[7:4]/GPIO2[27:30]	N28, P25, P26, P27	I/O	OV _{DD}				
TSEC1_TXD[3:0]	V28, V27, V26, W28	0	LV _{DD1}	10			
TSEC1_TX_EN	W27	0	LV _{DD1}				
TSEC1_TX_ER/GPIO2[31]	N24	I/O	OV _{DD}				
Three-Spee	ed Ethernet Controller (Gigabit Ethern	et 2)					
TSEC2_COL/GPIO1[21]	P28	I/O	OV _{DD}				
TSEC2_CRS/GPIO1[22]	AC28	I/O	LV _{DD2}				
TSEC2_GTX_CLK	AC27	0	LV _{DD2}				
TSEC2_RX_CLK	AB25	I	LV _{DD2}				
TSEC2_RX_DV/GPIO1[23]	AC26	I/O	LV _{DD2}				
TSEC2_RXD[7:4]/GPIO1[26:29]	R28, T24, T25, T26	I/O	OV _{DD}				
TSEC2_RXD[3:0]/GPIO1[13:16]	AA25, AA26, AA27, AA28	I/O	LV _{DD2}				
TSEC2_RX_ER/GPIO1[25]	R25	I/O	OV _{DD}				
TSEC2_TXD[7]/GPIO1[31]	T27	I/O	OV _{DD}				
TSEC2_TXD[6]/DR_XCVR_TERM_SEL	T28	0	OV _{DD}				
TSEC2_TXD[5]/DR_UTMI_OPMODE1	U28	0	OV _{DD}				
TSEC2_TXD[4]/DR_UTMI_OPMODE0	U27	0	OV _{DD}				
TSEC2_TXD[3:0]/GPIO1[17:20]	AB26, AB27, AA24, AB28	I/O	LV _{DD2}				
TSEC2_TX_ER/GPIO1[24]	R27	I/O	OV _{DD}				
TSEC2_TX_EN/GPIO1[12]	AD28	I/O	LV _{DD2}	3			
TSEC2_TX_CLK/GPIO1[30]	R26	I/O	OV _{DD}				
	DUART						
UART_SOUT[1:2]/MSRCID[0:1]/LSRCID[0:1]	B4, A4	0	OV _{DD}				
UART_SIN[1:2]/MSRCID[2:3]/LSRCID[2:3]	D5, C5	I/O	OV _{DD}				
UART_CTS[1]/MSRCID4/LSRCID4	B5	I/O	OV _{DD}				
UART_CTS[2]/MDVAL/LDVAL	A5	I/O	OV _{DD}				
UART_RTS[1:2]	D6, C6	0	OV _{DD}				
I ² C interface							
IIC1_SDA	E5	I/O	OV _{DD}	2			
IIC1_SCL	A6	I/O	OV _{DD}	2			
IIC2_SDA	B6	I/O	OV _{DD}	2			
IIC2_SCL	E7	I/O	OV _{DD}	2			
	SPI						
SPIMOSI	D7	I/O	OV _{DD}				

As shown in Figure 41, the primary clock input (frequency) is multiplied up by the system phase-locked loop (PLL) and the clock unit to create the coherent system bus clock (csb_clk), the internal clock for the DDR controller (ddr_clk), and the internal clock for the local bus interface unit ($lbiu_clk$).

The *csb_clk* frequency is derived from a complex set of factors that can be simplified into the following equation:

 $csb_clk = \{PCI_SYNC_IN \times (1 + CFG_CLKIN_DIV)\} \times SPMF$

In PCI host mode, PCI_SYNC_IN \times (1 + CFG_CLKIN_DIV) is the CLKIN frequency.

The *csb_clk* serves as the clock input to the e300 core. A second PLL inside the e300 core multiplies the *csb_clk* frequency to create the internal clock for the e300 core (*core_clk*). The system and core PLL multipliers are selected by the SPMF and COREPLL fields in the reset configuration word low (RCWL), which is loaded at power-on reset or by one of the hard-coded reset options. See the chapter on reset, clocking, and initialization in the *MPC8349E Reference Manual* for more information on the clock subsystem.

The internal *ddr_clk* frequency is determined by the following equation:

 $ddr_clk = csb_clk \times (1 + RCWL[DDRCM])$

 ddr_clk is not the external memory bus frequency; ddr_clk passes through the DDR clock divider (÷2) to create the differential DDR memory bus clock outputs (MCK and MCK). However, the data rate is the same frequency as ddr_clk .

The internal *lbiu_clk* frequency is determined by the following equation:

 $lbiu_clk = csb_clk \times (1 + RCWL[LBIUCM])$

lbiu_clk is not the external local bus frequency; *lbiu_clk* passes through the LBIU clock divider to create the external local bus clock outputs (LSYNC_OUT and LCLK[0:2]). The LBIU clock divider ratio is controlled by LCCR[CLKDIV].

In addition, some of the internal units may have to be shut off or operate at lower frequency than the csb_clk frequency. Those units have a default clock ratio that can be configured by a memory-mapped register after the device exits reset. Table 53 specifies which units have a configurable clock frequency.

Unit	Default Frequency	Options
TSEC1	csb_clk/3	Off, csb_clk, csb_clk/2, csb_clk/3
TSEC2, I ² C1	csb_clk/3	Off, csb_clk, csb_clk/2, csb_clk/3
Security core	csb_clk/3	Off, csb_clk, csb_clk/2, csb_clk/3
USB DR, USB MPH	csb_clk/3	Off, csb_clk, csb_clk/2, <i>csb_clk/3</i>
PCI and DMA complex	csb_clk	Off, <i>csb_clk</i>

Table 53. Configurable Clock Units

_	•	-		
Characteristic	Symbol	Value	Unit	Notes
Junction-to-case thermal	$R_{ extsf{ heta}JC}$	5	°C/W	5
Junction-to-package natural convection on top	Ψіт	5	°C/W	6

Table 62. Package Thermal Characteristics for PBGA (continued)

Notes

- 1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
- 2. Per SEMI G38-87 and JEDEC JESD51-2 with the single-layer board horizontal.
- 3. Per JEDEC JESD51-6 with the board horizontal.
- 4. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
- 5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
- 6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

20.2 Thermal Management Information

For the following sections, $P_D = (V_{DD} \times I_{DD}) + P_{I/O}$ where $P_{I/O}$ is the power dissipation of the I/O drivers. See Table 5 for I/O power dissipation values.

20.2.1 Estimation of Junction Temperature with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature, T_J, can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

 T_J = junction temperature (°C)

 T_A = ambient temperature for the package (°C)

 $R_{\theta IA}$ = junction-to-ambient thermal resistance (°C/W)

 P_D = power dissipation in the package (W)

The junction-to-ambient thermal resistance is an industry-standard value that provides a quick and easy estimation of thermal performance. Generally, the value obtained on a single-layer board is appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity $T_J - T_A$) are possible.

20.2.2 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For

System Design Information

21 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8347E.

21.1 System Clocking

The MPC8347E includes two PLLs:

- 1. The platform PLL generates the platform clock from the externally supplied CLKIN input. The frequency ratio between the platform and CLKIN is selected using the platform PLL ratio configuration bits as described in Section 19.1, "System PLL Configuration."
- 2. The e300 core PLL generates the core clock as a slave to the platform clock. The frequency ratio between the e300 core clock and the platform clock is selected using the e300 PLL ratio configuration bits as described in Section 19.2, "Core PLL Configuration."

21.2 PLL Power Supply Filtering

Each PLL gets power through independent power supply pins (AV_{DD}1, AV_{DD}2, respectively). The AV_{DD} level should always equal to V_{DD} , and preferably these voltages are derived directly from V_{DD} through a low frequency filter scheme.

There are a number of ways to provide power reliably to the PLLs, but the recommended solution is to provide four independent filter circuits as illustrated in Figure 42, one to each of the four AV_{DD} pins. Independent filters to each PLL reduce the opportunity to cause noise injection from one PLL to the other.

The circuit filters noise in the PLL resonant frequency range from 500 kHz to 10 MHz. It should be built with surface mount capacitors with minimum effective series inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

To minimize noise coupled from nearby circuits, each circuit should be placed as closely as possible to the specific AV_{DD} pin being supplied. It should be possible to route directly from the capacitors to the AV_{DD} pin, which is on the periphery of package, without the inductance of vias.

Figure 42 shows the PLL power supply filter circuit.



Figure 42. PLL Power Supply Filter Circuit

Revision	Date	Substantive Change(s)		
1	4/2005	Table 1: Addition of note 1Table 48: Addition of Therm0 (K32)Table 49: Addition of Therm0 (B15)		
0	4/2005	Initial release.		

Table 66. Document Revision History (continued)

Ordering Information

Table	68.	SVR	Settings	(continued))
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MPC8347E	PBGA	8054_0010
MPC8347	PBGA	8055_0010

23.2 Part Marking

Parts are marked as in the example shown in Figure 44.



Figure 44. Freescale Part Marking for TBGA or PBGA Devices

Ordering Information

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